

**METHODS OF FORMING HIGH DENSITY METAL WIRING FOR FINE LINE
AND SPACE PACKAGING APPLICATIONS AND STRUCTURES FORMED
THEREBY**

ABSTRACT

Methods of forming microelectronic device structures are described. Those methods may include forming at least one opening through a build up structure and a photo sensitive material disposed on the build up structure, wherein the build up structure comprises a portion of a package substrate, filling the at least one opening with a metal containing nanopaste, and sintering the metal containing nanopaste to form a bulk property metal structure in the at least one opening.

FIG. 2b